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Altri autori (Persone)	FisherD. J
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Nota di bibliografia	Includes bibliographical references and indexes.
Nota di contenuto	Dislocation Reactions and Stacking-Fault Energies; Table of Contents; Parameters of Interaction with Vacancies in Tungsten of Homovalent Atomic Probes from the VIB and VIIB Groups of the Periodic Table; Study of Production Defects in Pure Aluminum and 3003 Aluminum Alloy by Electrical Measurements; Study of Nanocrystalline NiAl Alloys Prepared by Mechanical Alloying; Estimating the Activation Enthalpy for Defect Formation in 5754 Alloys by Using Nuclear, Electrical and Mechanical Methods; Defect Analysis of 316LSS during the Powder Injection Moulding Process Effect of Hydrogen on the Microhardness of Tin Brass Heat Exchanger TubeCorrelation between Nuclear and Electrical Methods for Estimating the Activation Enthalpy of Defect Formation in 2024 Alloys; Artificial Ageing Effect on Mechanical, Electrical Properties and Positron Lifetime of Aircraft 2024 Alloy; Natural Convection Flow Simulation of Nanofluid in a Square Cavity Using an Incompressible Generalized Lattice Boltzmann Method; A Review of some Theoretical Models for Point Defect Calculations The Diffusion Problem of New Phase Inclusion Growth in Bounded Regions of Oversaturated Solid SolutionPressureless Sintering and Characterization of Al2O3-SiO2-ZrO2 Composite; Electrical Properties of Zr-Doped La2O3 Nanocrystallites as a Good Gate Dielectric; Effect of Post-Deposition Annealing on some Optical Properties of Thermally-

	Evaporated V2O5 Thin Film; Electrical Conductivity and Phase Transition Studies in the ZrO2-CdO System; Growth of ZnO Thin Films on Silicon Substrates by Atomic Layer Deposition; Observation of Dielectric Peaks in Glassy Se70Te20Sn10 Alloy Theoretical Investigation of the Spin Hamiltonian Parameters for the Tetragonal [Fe(CN)4Cl2]5- Complex in NaCIAbstracts; Keywords Index; Authors Index
Sommario/riassunto	Volume 329 of the journal, Defect and Diffusion Forum, comprises a handy compilation of data on dislocation reactions, and stacking-fault energies for a wide range of materials including carbon, carbides, nitrides, oxides, silica, silicates and borides. It also contains original papers on the Interaction with Vacancies in Tungsten, Defects in Pure Aluminum and 3003 Aluminum Alloy, Nanocrystalline NiAl Alloys Prepared by Mechanical Alloying, Activation Enthalpy for Defect Formation in 5754 Alloys, Defect Analysis of 316LSS during Powder Injection Moulding, Effect of Hydrogen on the Microhardnes